Jacopo Frascaroli

List of Publications by Year
in descending order

23	593	687363 13	752698 20
papers	citations	h-index	g-index

23	23	23	903
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Resistive Random Access Memory (RRAM) Technology: From Material, Device, Selector, 3D Integration to Bottom-Up Fabrication. Kluwer International Series in Electronic Materials: Science and Technology, 2022, , 33-64.	0.5	1
2	Automatic Defect Detection in Epitaxial Layers by Micro Photoluminescence Imaging. IEEE Transactions on Semiconductor Manufacturing, 2022, 35, 540-545.	1.7	3
3	(Invited) Impact of the Substrate Specifications on the Extended Defects Induced by the Deep Trench Isolation. ECS Transactions, 2021, 102, 29-36.	0.5	1
4	Internal and External Gettering of Iron Contamination in Power Technologies. Physica Status Solidi (A) Applications and Materials Science, 2021, 218, 2100206.	1.8	2
5	Electrical AFM for the Analysis of Resistive Switching. Nanoscience and Technology, 2019, , 205-229.	1.5	2
6	Stimulated Ionic Telegraph Noise in Filamentary Memristive Devices. Scientific Reports, 2019, 9, 6310.	3.3	20
7	Extended memory lifetime in spiking neural networks employing memristive synapses with nonlinear conductance dynamics. Nanotechnology, 2019, 30, 015102.	2.6	33
8	Hafnium Impurity Defects in Silicon: A Characterization. ECS Journal of Solid State Science and Technology, 2018, 7, P583-P587.	1.8	0
9	Spike-driven threshold-based learning with memristive synapses and neuromorphic silicon neurons. Journal Physics D: Applied Physics, 2018, 51, 344003.	2.8	23
10	Evidence of soft bound behaviour in analogue memristive devices for neuromorphic computing. Scientific Reports, 2018, 8, 7178.	3.3	54
11	(Invited) Analog HfO2-RRAM Switches for Neural Networks. ECS Transactions, 2017, 75, 85-94.	0.5	15
12	Role of Al doping in the filament disruption in HfO₂resistance switches. Nanotechnology, 2017, 28, 395202.	2.6	36
13	Resistive random access memory (RRAM) technology: From material, device, selector, 3D integration to bottom-up fabrication. Journal of Electroceramics, 2017, 39, 21-38.	2.0	79
14	Modeling of phosphorus diffusion in silicon oxide and incorporation in silicon nanocrystals. Journal of Materials Chemistry C, 2016, 4, 3531-3539.	5.5	10
15	Ozone-Based Sequential Infiltration Synthesis of Al₂O₃ Nanostructures in Symmetric Block Copolymer. ACS Applied Materials & Interfaces, 2016, 8, 33933-33942.	8.0	29
16	Role of metal-oxide interfaces in the multiple resistance switching regimes of Pt/HfO2/TiN devices. Applied Physics Letters, 2015, 107, .	3.3	78
17	Resistive Switching in High-Density Nanodevices Fabricated by Block Copolymer Self-Assembly. ACS Nano, 2015, 9, 2518-2529.	14.6	72
18	Thermodynamic stability of high phosphorus concentration in silicon nanostructures. Nanoscale, 2015, 7, 14469-14475.	5.6	33

#	Article	IF	Citations
19	Effect of Al doping on the retention behavior of HfO2 resistive switching memories. Microelectronic Engineering, 2015, 147, 104-107.	2.4	52
20	Fabrication of periodic arrays of metallic nanoparticles by block copolymer templates on HfO₂substrates. Nanotechnology, 2015, 26, 215301.	2.6	11
21	Quantification of phosphorus diffusion and incorporation in silicon nanocrystals embedded in silicon oxide. Surface and Interface Analysis, 2014, 46, 393-396.	1.8	26
22	Surface passivation for ultrathin Al₂O₃ layers grown at low temperature by thermal atomic layer deposition. Physica Status Solidi (A) Applications and Materials Science, 2013, 210, 732-736.	1.8	13
23	Microâ€photoluminescence imaging at room temperature of crystallographic defects generated by deep trench structures. Physica Status Solidi (A) Applications and Materials Science, 0, , .	1.8	0